v ̈Ω Parameter	ϒ N Symbol	̈ΩӨ Rating	D Ӌ Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current(DC)	I_D(T_C=25)	275	A
	I_D(T_C=100)	194	A
Drain Current – Pulsed	I_{DM}	1100	A
Power Dissipation	P_{tot}	263	W
Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 175	ł
Continuous-Source Current	I_S	275	A
Single Pulse Avalanche Energy (V_{DD}=50V,L=1.0mH)	E_{AS}	2450	mJ
Thermal resistance, junction - Ambient	R JA	45	ł 2 Z
Thermal resistance, junction - case	R JC	0.57	

v ̈Ω Parameter	ϒ N Symbol	Ӆ :ˆ ϯ Test Conditions	ѡ ṇ Ө Min	Ɛ ʒ Ө Typ	ѡ ᶻ Ө Max	D Ӌ Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250uA, V_{GS}=0V	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	2		4	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V, V_{GS}=0V			1	uA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}= ±20V			±100	nA

/ Electrical Characteristic Curve

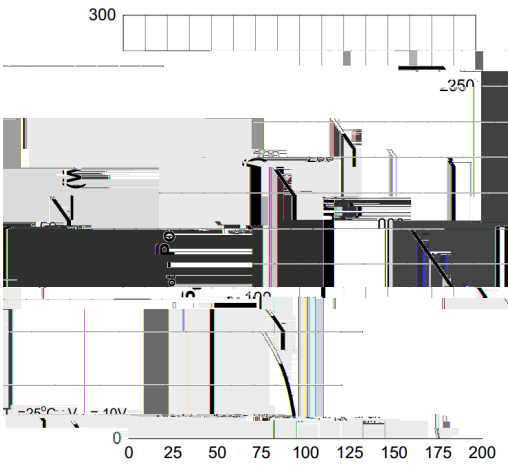


Fig2. Current Capability

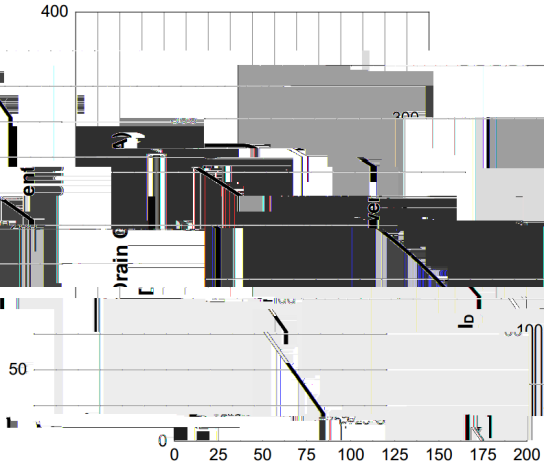


Fig1. Power Capability

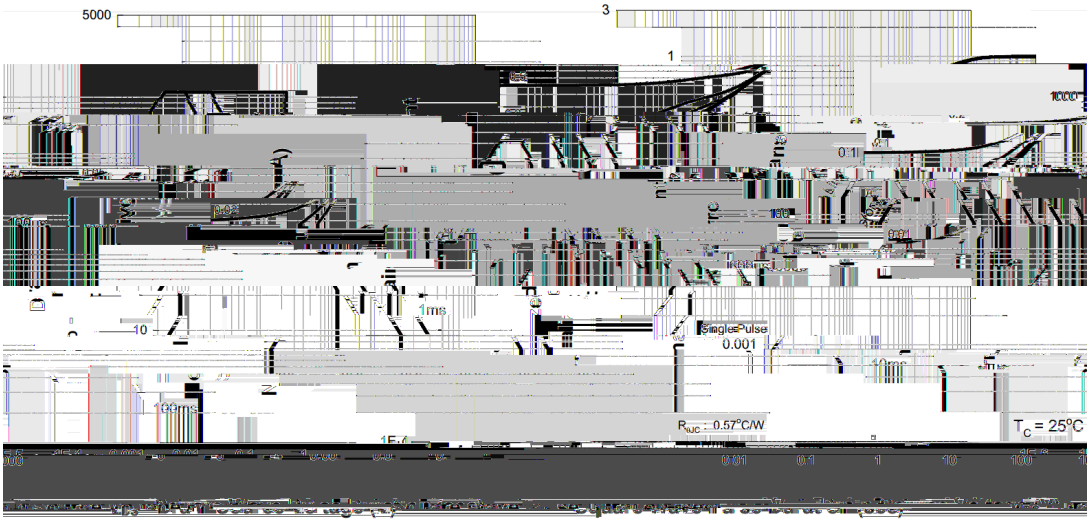
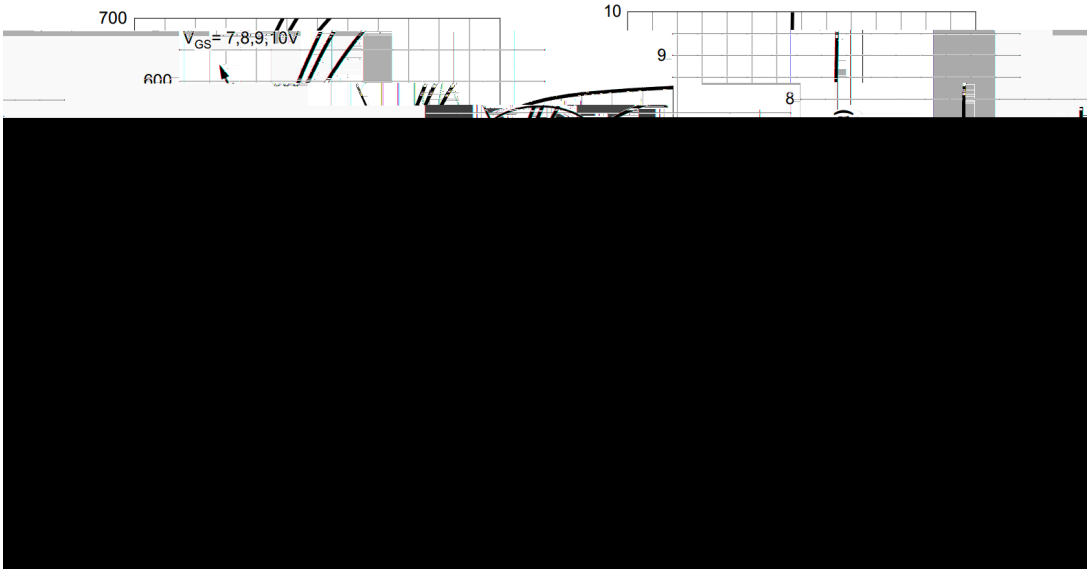


Fig3. Safe Operating Area

Fig4. Transient Thermal Impedance



/ Electrical Characteristic Curve

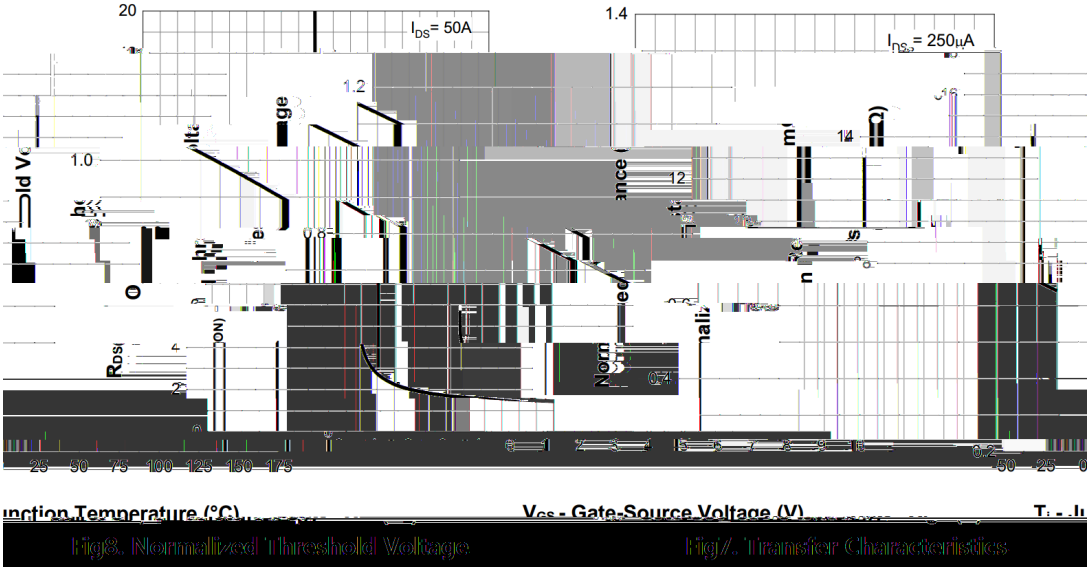
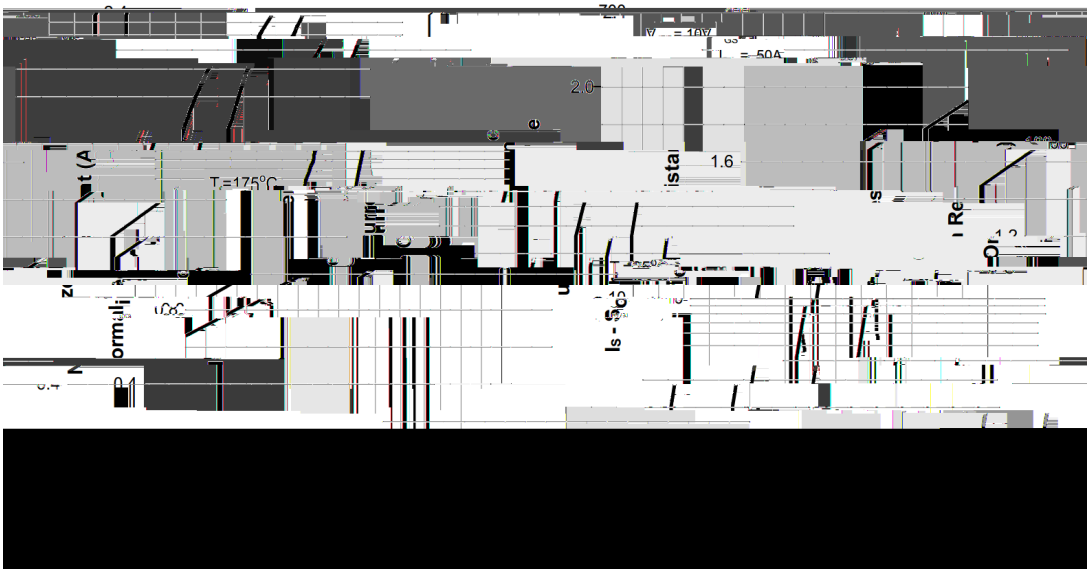


Fig8. Normalized Threshold Voltage Fig7. Transfer Characteristics



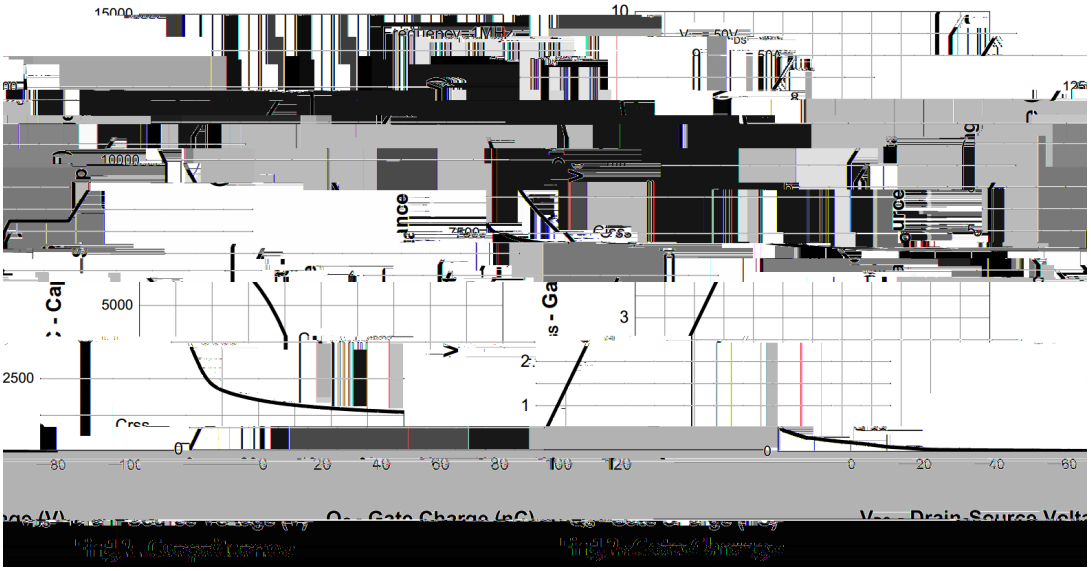
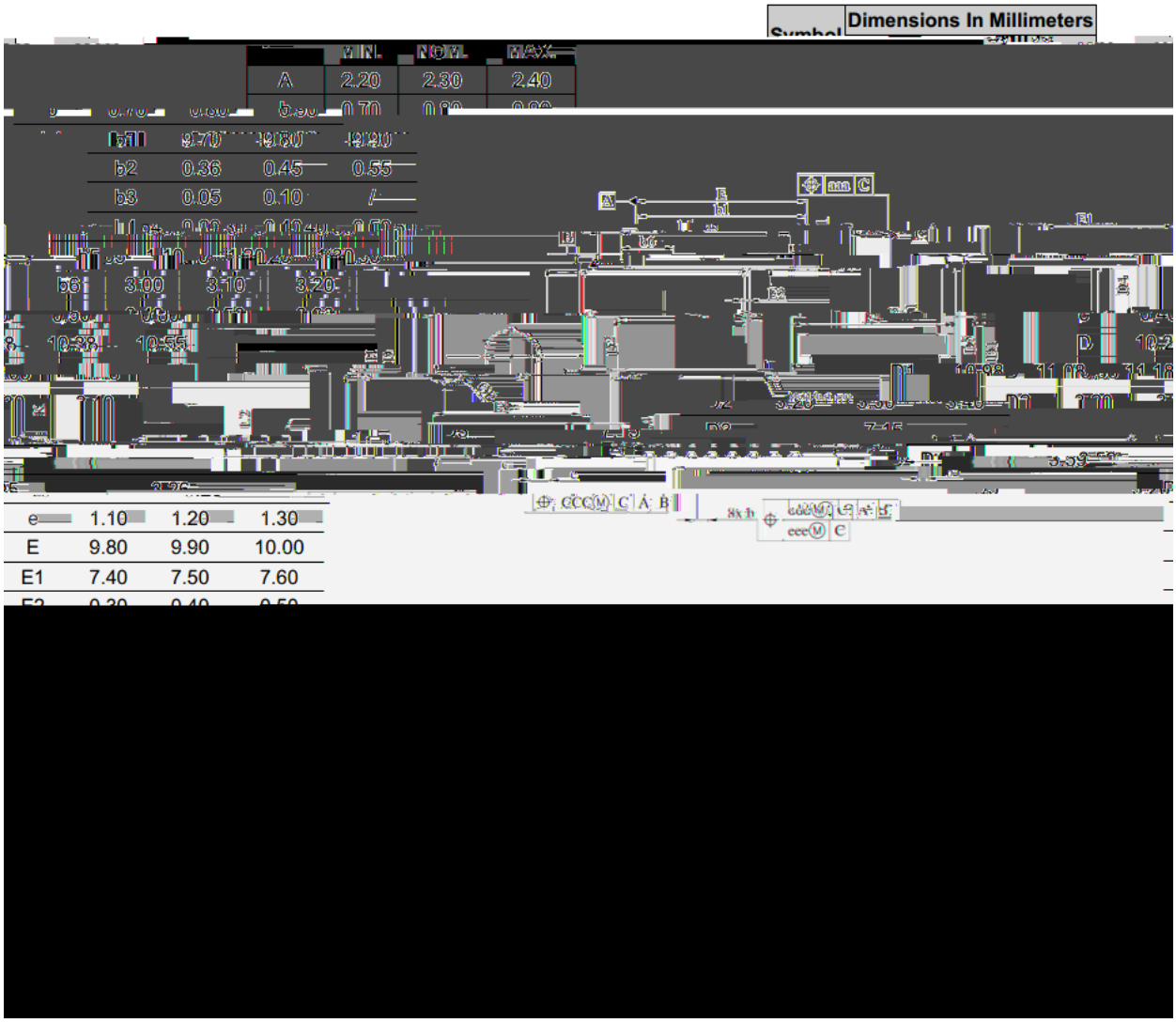
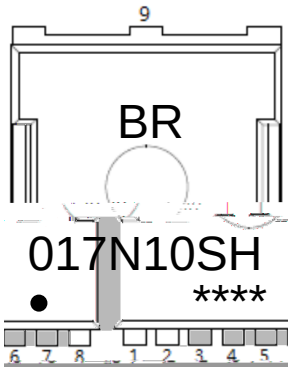


Fig9. Capacitance Fig10. Gate Charge

/ Package Dimensions



/ Marking Instructions



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EU χ	ʜʂ ɜ ᴎ ᑎ
017N10SH χ	ʜʂ ʒ ᴺ ᑎ
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Note χ	
BR χ	Company Code
017N10SH χ	Product Type Code
****:	Lot No. Code, code change with Lot No.